CPH3360

Power MOSFET
–30V, 303mΩ, –1.6A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- High Speed Switching
- 4V drive
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

- DC/DC Converter

ON Semiconductor®

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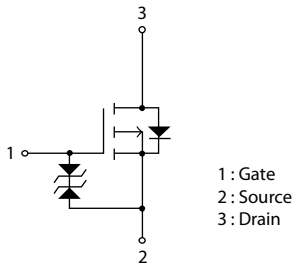
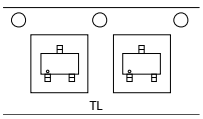
V_{DSS}	R_{DS}(on) Max	I_D Max
–30V	303mΩ@ –10V	–1.6A
	532mΩ@ –4.5V	
	617mΩ@ –4V	

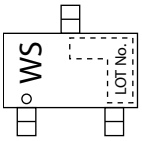
ELECTRICAL CONNECTION
P-Channel



PACKING TYPE : TL



MARKING



ORDERING INFORMATION
See detailed ordering and shipping information on page 5 of this data sheet.

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DSS}	–30	V
Gate to Source Voltage	V_{GSS}	±20	V
Drain Current (DC)	I_D	–1.6	A
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%	I_{DP}	–6.4	A
Power Dissipation When mounted on ceramic substrate (900mm^2 × 0.8mm)	P_D	0.9	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
2 : This product is designed to "ESD immunity<200V*", so please take care when handling.
*Machine Model

THERMAL RESISTANCE RATINGS

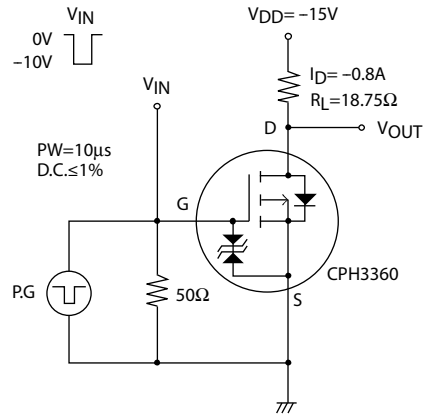
Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm^2 × 0.8mm)	$R_{\theta JA}$	138.8	°C/W

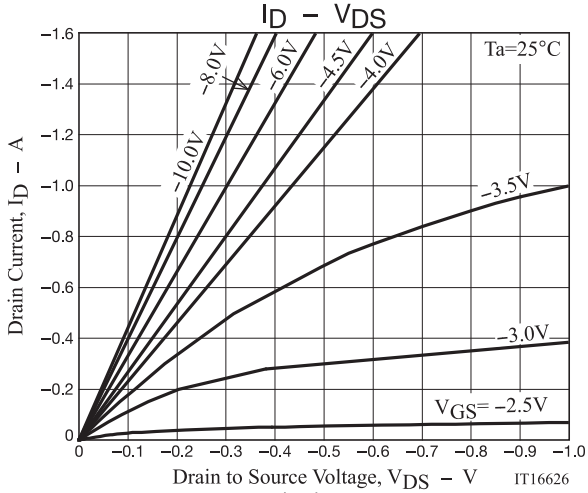
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

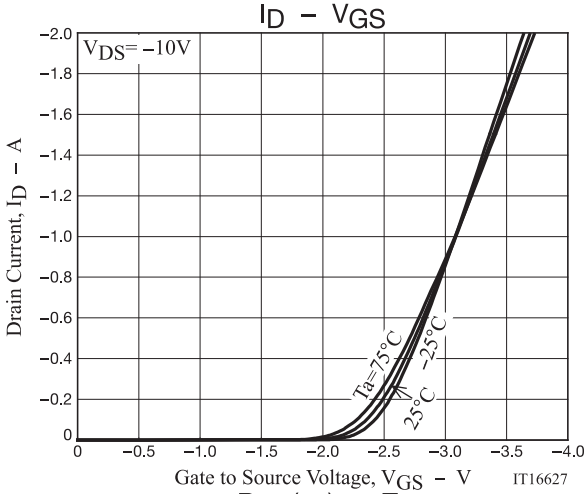
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−30V, V_{GS}=0V			−1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Gate Threshold Voltage	$V_{GS}(th)$	V_{DS}=−10V, I_D=−1mA	−1.2		−2.6	V
Forward Transconductance	g_{FS}	V_{DS}=−10V, I_D=−0.8A		1.3		S
Static Drain to Source On-State Resistance	$R_{DS}(on)1$	I_D=−0.8A, V_{GS}=−10V		233	303	mΩ
	$R_{DS}(on)2$	I_D=−0.4A, V_{GS}=−4.5V		380	532	mΩ
	$R_{DS}(on)3$	I_D=−0.4A, V_{GS}=−4V		441	617	mΩ
Input Capacitance	Ciss	V_{DS}=−10V, f=1MHz		82		pF
Output Capacitance	Coss			22		pF
Reverse Transfer Capacitance	Crss			16		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		4.0		ns
Rise Time	t_r			3.3		ns
Turn-OFF Delay Time	$t_d(off)$			12		ns
Fall Time	t_f			5.4		ns
Total Gate Charge	Qg	V_{DS}=−15V, V_{GS}=−10V, I_D=−1.6A		2.2		nC
Gate to Source Charge	Qgs			0.36		nC
Gate to Drain “Miller” Charge	Qgd			0.49		nC
Forward Diode Voltage	V_{SD}	I_S=−1.6A, V_{GS}=0V		−0.9	−1.5	V

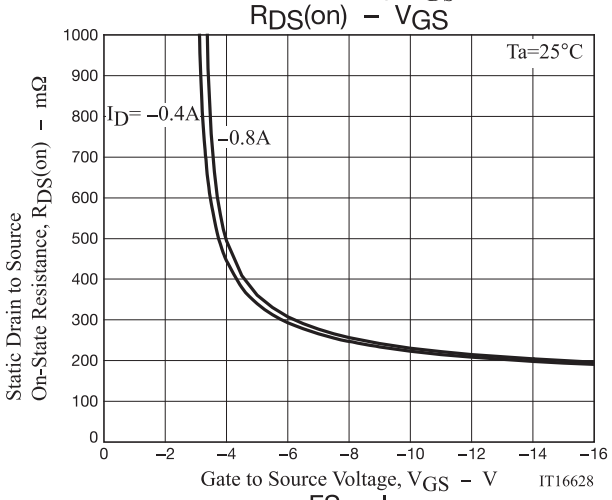
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

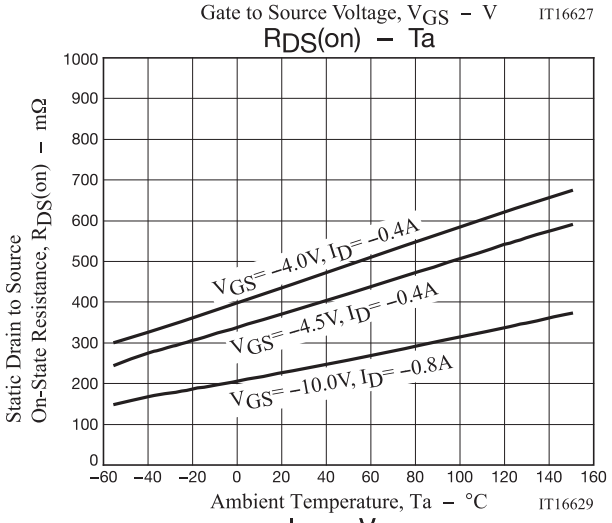
Switching Time Test Circuit

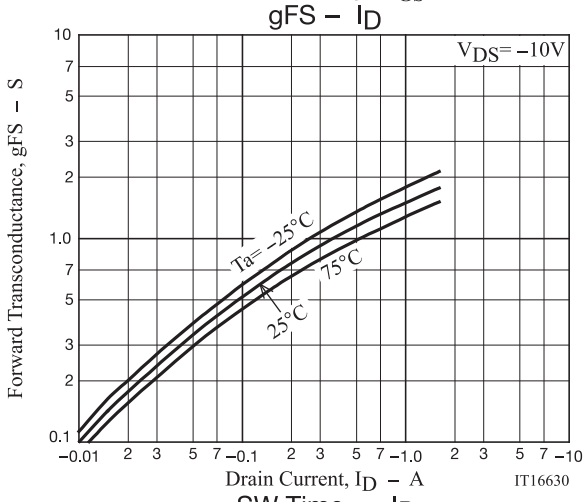


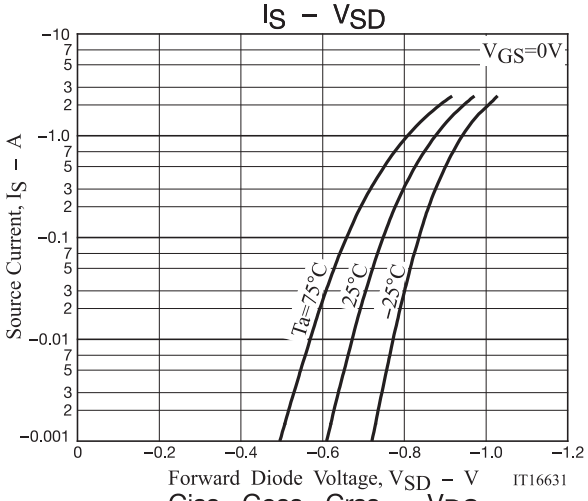

ID – VDS
Ta=25°C
–8.0V
–6.0V
–4.5V
–4.0V
–10.0V
–3.5V
–3.0V
VGS= –2.5V
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT16626

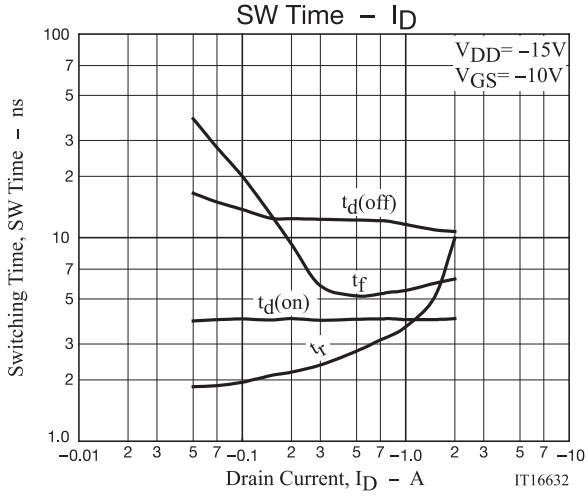

ID – VGS
VDS= –10V
Ta=75°C
–25°C
25°C
Drain Current, ID – A
Gate to Source Voltage, VGS – V
IT16627

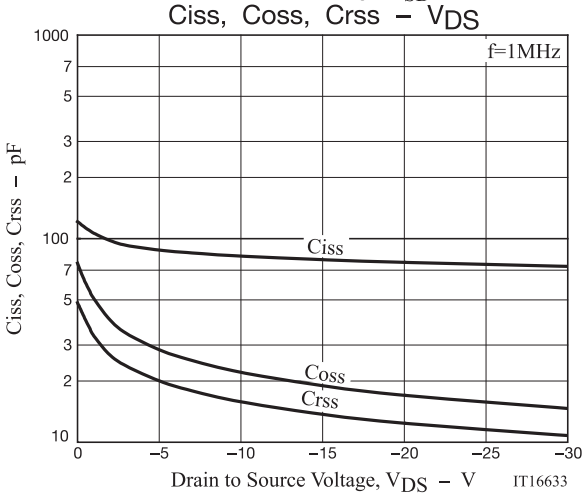

RDS(on) – VGS
Ta=25°C
ID= –0.4A
–0.8A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Gate to Source Voltage, VGS – V
IT16628

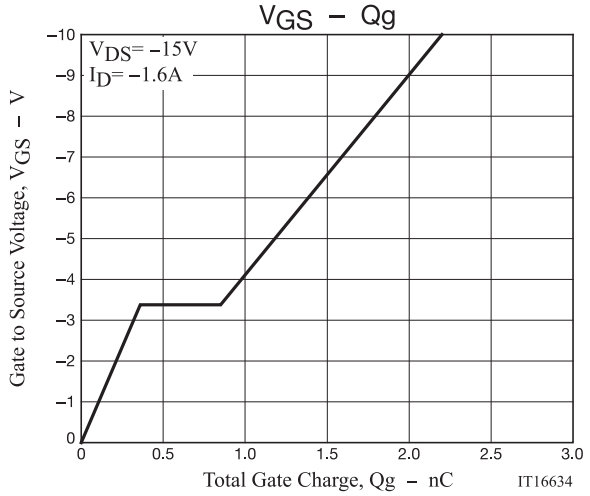

RDS(on) – Ta
VGS= –4.0V, ID= –0.4A
VGS= –4.5V, ID= –0.4A
VGS= –10.0V, ID= –0.8A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT16629

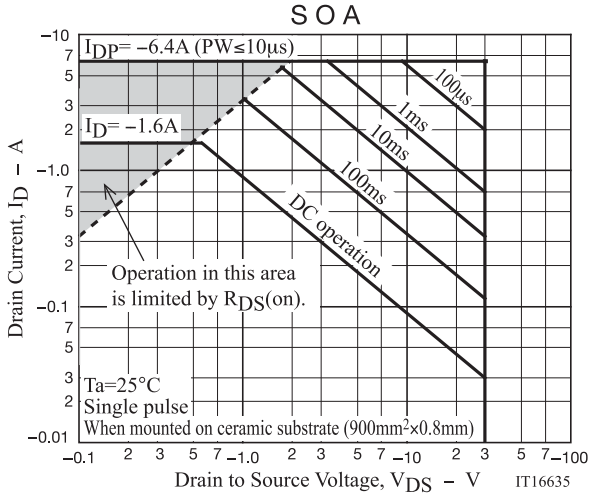

gFS – ID
VDS= –10V
Ta= –25°C
75°C
25°C
Forward Transconductance, gFS – S
Drain Current, ID – A
IT16630

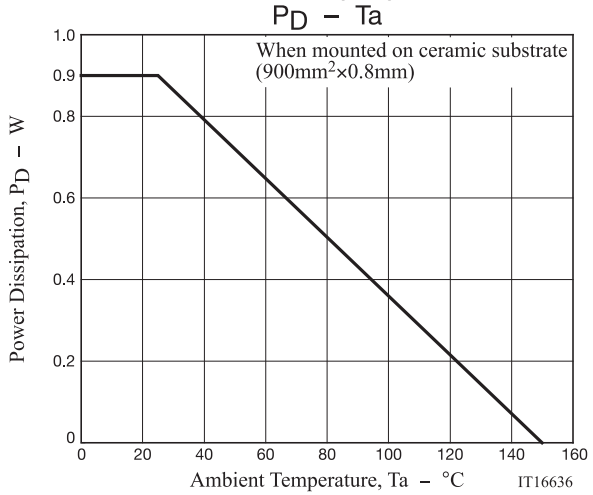

IS – VSD
VGS=0V
Ta=75°C
25°C
–25°C
Source Current, IS – A
Forward Diode Voltage, VSD – V
IT16631

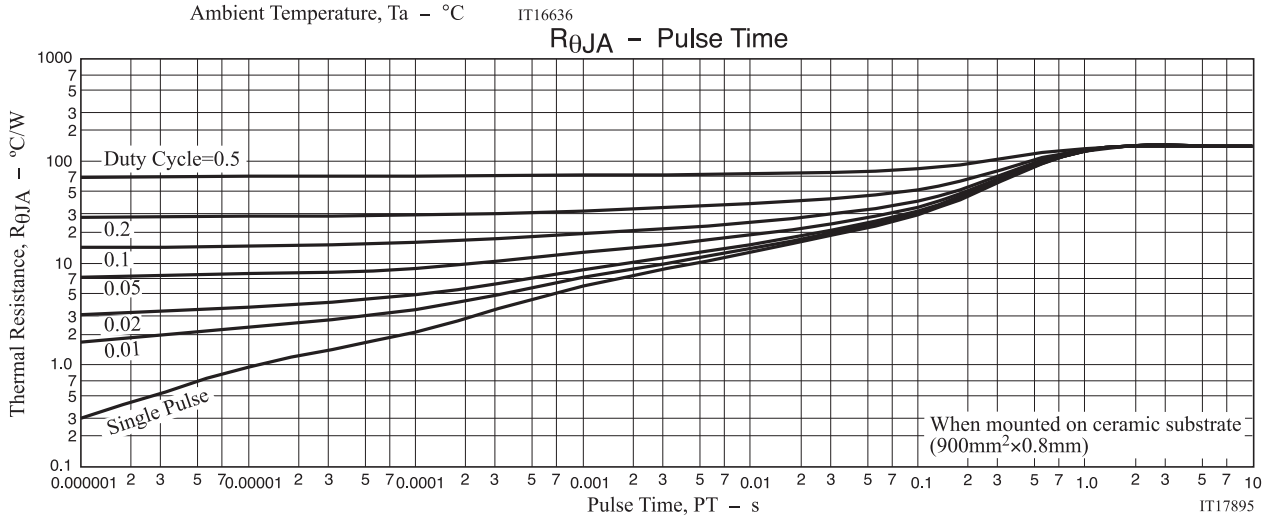

SW Time – ID
VDD= –15V
VGS= –10V
td(off)
tf
td(on)
tr
Switching Time, SW Time – ns
Drain Current, ID – A
IT16632


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain to Source Voltage, VDS – V
IT16633


VGS – Qg
VDS= –15V
ID= –1.6A
Gate to Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT16634


S O A
IDP= –6.4A (PW≤10μs)
ID= –1.6A
100μs
1ms
10ms
100ms
DC operation
Operation in this area
is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (900mm2×0.8mm)
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT16635

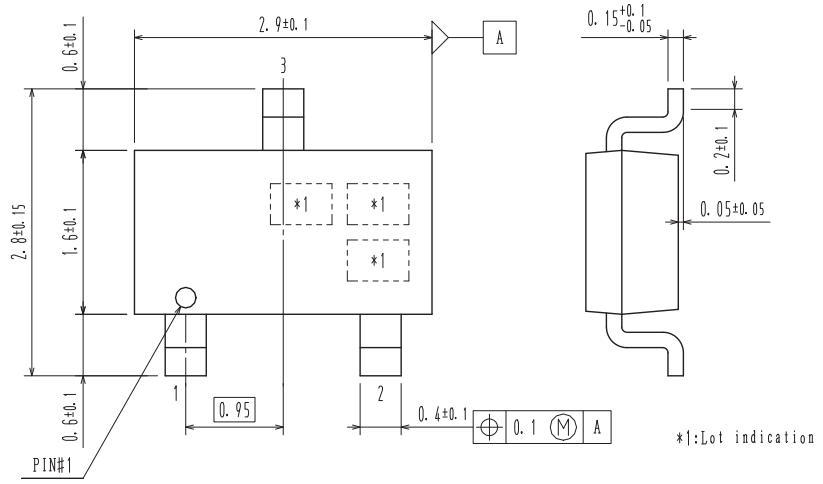

PD – Ta
When mounted on ceramic substrate
(900mm2×0.8mm)
Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT16636


RθJA – Pulse Time
Duty Cycle=0.5
0.2
0.1
0.05
0.02
0.01
Single Pulse
When mounted on ceramic substrate
(900mm2×0.8mm)
Thermal Resistance, RθJA – °C/W
Pulse Time, PT – s
IT17895

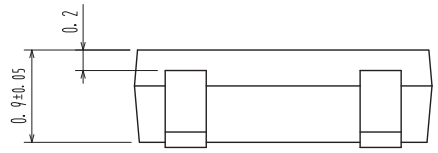
PACKAGE DIMENSIONS

unit : mm

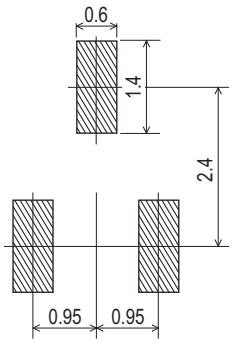
CPH3
CASE 318BA
ISSUE O



1 : Gate
2 : Source
3 : Drain



Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
CPH3360-TL-H	WS	CPH3 SC-59, SOT-23, TO-236 (Pb-Free / Halogen Free)	3,000 / Tape & Reel
CPH3360-TL-W			

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the CPH3360 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.